

# 80 mA, Tiny CMOS LDO With Shutdown

#### Features

- AEC-Q100 Automotive Qualified, See Product Identification System
- Space-Saving 5-Pin SC-70 and SOT-23
   Packages
- Extremely Low Operating Current for Longer Battery Life: 53 µA (typical)
- Very Low Dropout Voltage
- Rated 80 mA Output Current
- Requires only 1 µF Ceramic Output Capacitance
- High Output Voltage Accuracy: ±0.5% (typical)
- 10 µsec (typical) Wake-Up Time from SHDN
- Power-Saving Shutdown Mode: 0.05 µA (typical)
- Overcurrent and Overtemperature Protection
- · Pin Compatible Upgrade for Bipolar Regulators

#### Applications

- Automotive
- Cellular/GSM/PHS Phones
- Battery-operated Systems
- Portable Computers
- Medical Instruments
- Electronic Games
- Pagers

#### **General Description**

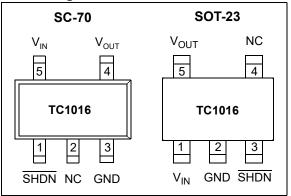
The TC1016 is a high-accuracy (typically  $\pm 0.5\%$ ), CMOS upgrade for bipolar low dropout regulators (LDOs). The TC1016 is offered in both the SC-70 and SOT-23 packages. The SC-70 package represents a 50% footprint reduction versus the popular SOT-23 package.

Developed specifically for battery-powered systems, the device's CMOS construction consumes only 53  $\mu$ A typical supply current over the entire 80 mA operating load range. This can be as much as 60 times less than the quiescent operating current consumed by bipolar LDOs.

With small-space requirements and cost in mind, the TC1016 was developed to be stable over the entire input voltage and output current operating range using low value (1  $\mu$ F ceramic), low Equivalent Series Resistance (ESR) output capacitors. Additional integrated features (such as shutdown, overcurrent and overtemperature protection) further reduce board space and cost of the entire voltage-regulating application.

Key performance parameters for the TC1016 are low drop out voltage (150 mV (typ.) at 80 mA output current), low supply current while shutdown (0.05  $\mu$ A typical) and fast stable response to sudden input voltage and load changes.

#### **Pin Configurations**



# 1.0 ELECTRICAL CHARACTERISTICS

# ABSOLUTE MAXIMUM RATINGS<sup>†</sup>

Input Voltage	6.5V
Power Dissipation	Internally Limited (Note 7)
Operating Temperature	40°C < T <sub>J</sub> < 125°C
Storage Temperature	
Maximum Voltage On Any Pin	
ESD protection on all pins <sup>(1)</sup> :	
НВМ	±2 kV
MM	± 200V
CDM	±1.5 kV

**†** Notice: Static-sensitive device. Unused devices must be stored in conductive material. Protect devices from static discharge and static fields. Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to Absolute Maximum Rating Conditions for extended periods may affect device reliability

**Note 1:** Testing was performed per AEC-Q100 standard. ESD CDM was tested on the 5L SC-70 package. For additional information please contact your local Microchip sales office.

# **ELECTRICAL CHARACTERISTICS**

 $V_{IN} = V_R + 1V$ ,  $I_L = 100 \mu$ A,  $C_L = 1.0\mu$ F,  $\overline{SHDN} > V_{IH}$ ,  $T_A = 25^{\circ}$ C, unless otherwise noted. **Boldface** type specifications apply for junction temperatures of -40°C to +125°C.

Parameter	Sym.	Min.	Тур.	Max.	Units	Test Conditions
Input Operating Voltage	V <sub>IN</sub>	2.7	_	6.0	V	Note 1
Maximum Output Current	I <sub>OUTMAX</sub>	80	_	—	mA	
Output Voltage	V <sub>OUT</sub>	V <sub>R</sub> - 2.5%	V <sub>R</sub> ±0.5%	V <sub>R</sub> + 2.5%	V	Note 2
V <sub>OUT</sub> Temperature Coefficient	TCV <sub>OUT</sub>	_	40	—	ppm/°C	Note 3
Line Regulation	$(\Delta V_{OUT}/\Delta V_{IN})/V_{R}$	_	0.01	0.2	%/V	(V <sub>R</sub> + 1V) < V <sub>IN</sub> < 6V
Load Regulation (Note 4)	$\Delta V_{OUT}/V_{R}$	—	0.23	1	%	$I_L = 0.1 \text{ mA to } I_{OUTMAX}$
Dropout Voltage (Note 5)	V <sub>IN</sub> – V <sub>OUT</sub>	_	2	_	mV	I <sub>L</sub> = 100 μA
		—	100	200		I <sub>L</sub> = 50 mA
		—	150	300		I <sub>L</sub> = 80 mA
Supply Current	I <sub>IN</sub>	—	53	90	μA	$\overline{\text{SHDN}} = V_{\text{IH}}, I_{\text{L}} = 0$
Shutdown Supply Current	I <sub>INSD</sub>	_	0.05	0.5	μA	SHDN = 0V
Power Supply Rejection Ratio	PSRR	—	58	_	dB	f =1 kHz, I <sub>L</sub> = 50 mA
Wake-Up Time (from Shutdown mode)	t <sub>WK</sub>		10	_	μs	V <sub>IN</sub> = 5V, I <sub>L</sub> = 60 mA, C <sub>IN</sub> = 1 μF, C <sub>OUT</sub> = 1 μF, f = 100 Hz

**Note** 1: The minimum  $V_{IN}$  has to meet two conditions:  $V_{IN} \ge 2.7V$  and  $V_{IN} \ge (V_R + 2.5\%) + V_{DROPOUT}$ .

2: 
$$V_R$$
 is the regulator voltage setting. For example:  $V_R$  = 1.8V, 2.7V, 2.8V, 3.0V

3: 
$$TCV_{OUT} = \frac{(V_{OUTMAX} - V_{OUTMIN}) \times 10^{\circ}}{V_{OUT} \times \Delta T}$$

- 4: Regulation is measured at a constant junction temperature using low duty cycle pulse testing. Load regulation is tested over a load range from 0.1 mA to the maximum specified output current. Changes in output voltage due to heating effects are covered by the Thermal Regulation specification.
- 5: Dropout voltage is defined as the input-to-output differential at which the output voltage drops 2% below its nominal value at a 1V differential.
- 6: Thermal regulation is defined as the change in output voltage at a time T after a change in power dissipation is applied, excluding load or line regulation effects. Specifications are for a current pulse equal to Ilmax at  $V_{IN} = 6V$  for t = 10 msec.
- 7: The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable juction temperature and the thermal resistance from junction-to-air (i.e. T<sub>A</sub>, T<sub>J</sub>, θ<sub>JA</sub>). Exceeding the maximum allowable power dissipation causes the device to initiate thermal shutdown. Please see Section 5.0 "Thermal Considerations" of this data sheet for more details.

### ELECTRICAL CHARACTERISTICS (CONTINUED)

 $V_{IN} = V_R + 1V$ ,  $I_L = 100 \mu$ A,  $C_L = 1.0\mu$ F,  $\overline{SHDN} > V_{IH}$ ,  $T_A = 25^{\circ}$ C, unless otherwise noted. **Boldface** type specifications apply for junction temperatures of -40^{\circ}C to +125°C.

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Parameter	Sym.	Min.	Тур.	Max.	Units	Test Conditions
Settling Time (from Shutdown Mode)	t <sub>S</sub>	—	32	—	μs	V <sub>IN</sub> = 5V, I <sub>L</sub> = 60 mA,C <sub>IN</sub> = 1 μF, C <sub>OUT</sub> = 1 μF, f = 100 Hz
Output Short Circuit Current	I <sub>OUTSC</sub>	—	120	—	mA	V <sub>OUT</sub> = 0V
Thermal Regulation	V <sub>OUT</sub> /P <sub>D</sub>	_	0.04	_	V/W	Notes 6, 7
Thermal Shutdown Die Temperature	T <sub>SD</sub>	—	160	—	°C	
Thermal Shutdown Hysteresis	$\Delta T_{SD}$	_	10	_	°C	
Output Noise	eN	—	800	—	nV/√Hz	f = 10 kHz
SHDN Input High Threshold	V <sub>IH</sub>	60	_	_	%V <sub>IN</sub>	V <sub>IN</sub> = 2.7V to 6.0V
SHDN Input Low Threshold	V <sub>IL</sub>	_	—	15	%V <sub>IN</sub>	V <sub>IN</sub> = 2.7V to 6.0V

Note 1:

The minimum V<sub>IN</sub> has to meet two conditions: V<sub>IN</sub>  $\ge 2.7V$  and V<sub>IN</sub>  $\ge (V_R + 2.5\%) + V_{DROPOUT}$ . V<sub>R</sub> is the regulator voltage setting. For example: V<sub>R</sub> = 1.8V, 2.7V, 2.8V, 3.0V. 2:

3: 
$$TCV_{OUT} = \frac{(V_{OUTMAX} - V_{OUTMIN}) \times 10^6}{V_{OUT} \times \Delta T}$$

4: Regulation is measured at a constant junction temperature using low duty cycle pulse testing. Load regulation is tested over a load range from 0.1 mA to the maximum specified output current. Changes in output voltage due to heating effects are covered by the Thermal Regulation specification.

Dropout voltage is defined as the input-to-output differential at which the output voltage drops 2% below its nominal value at a 1V 5: differential.

6: Thermal regulation is defined as the change in output voltage at a time T after a change in power dissipation is applied, excluding load or line regulation effects. Specifications are for a current pulse equal to Ilmax at  $V_{IN} = 6V$  for t = 10 msec. The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable juction temperature and the

7: thermal resistance from junction-to-air (i.e.  $T_A$ ,  $T_J$ ,  $\theta_{JA}$ ). Exceeding the maximum allowable power dissipation causes the device to initiate thermal shutdown. Please see Section 5.0 "Thermal Considerations" of this data sheet for more details.

#### TYPICAL PERFORMANCE CURVES 2.0

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

0.25

0.20

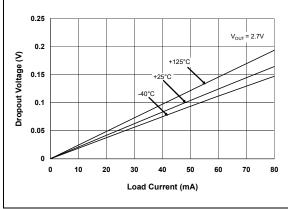


FIGURE 2-1: Dropout Voltage vs. Output Current.

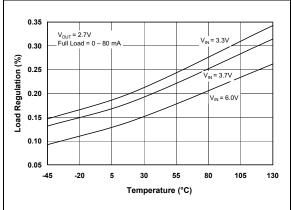


FIGURE 2-2: Load Regulation vs. Temperature.

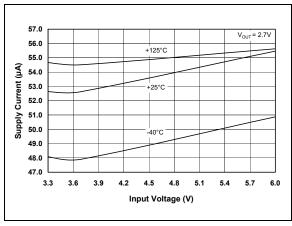
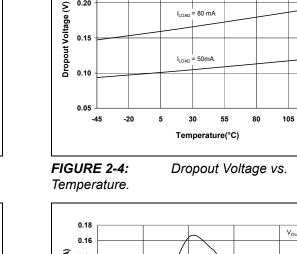
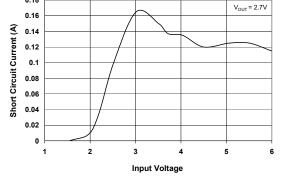


FIGURE 2-3: Supply Current vs. Input Voltage.





I<sub>LOAD</sub> = 80 mA

FIGURE 2-5: Input Voltage.

Short Circuit Current vs.

V<sub>OUT</sub> = 2.7V

130

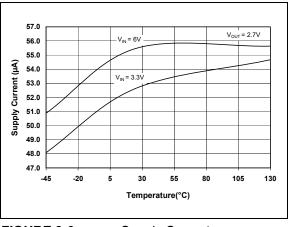


FIGURE 2-6: Temperature.

Supply Current vs.

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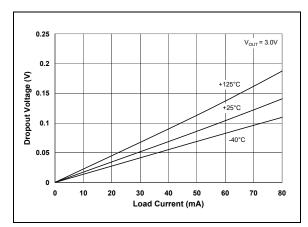


FIGURE 2-7: Dropout Voltage vs. Output Current.

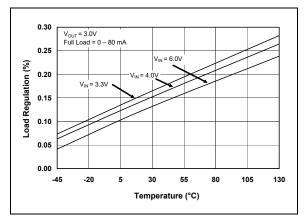
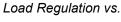


FIGURE 2-8: Temperature.



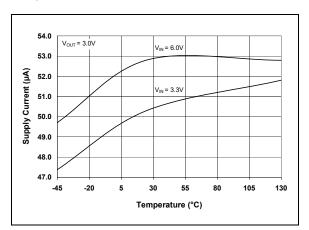
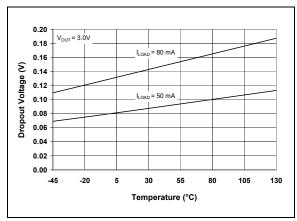


FIGURE 2-9: Temperature.

Supply Current vs.



*FIGURE 2-10:* Dropout Voltage vs. Temperature.

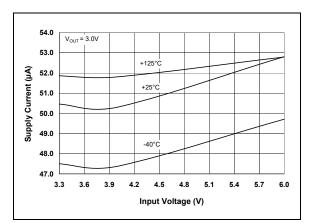


FIGURE 2-11: Supply Current vs. Input Voltage.

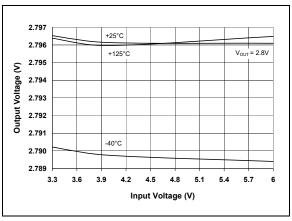


FIGURE 2-12: ( Voltage.

Output Voltage vs. Supply

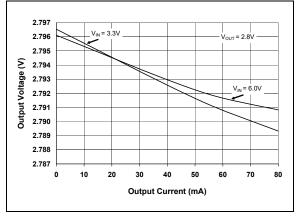


FIGURE 2-13: Output Voltage vs. Output Current.

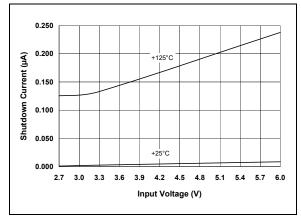


FIGURE 2-14: Shutdown Current vs. Input Voltage.

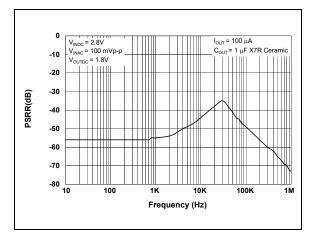
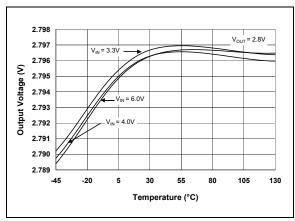


FIGURE 2-15: Power Supply Rejection Ratio vs. Frequency.



*FIGURE 2-16:* Output Voltage vs. *Temperature.* 

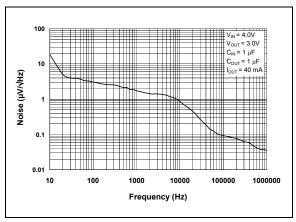


FIGURE 2-17: Output Noise

Output Noise vs. Frequency.

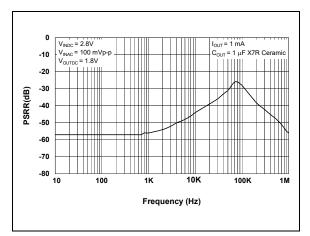


FIGURE 2-18: Power Supply Rejection Ratio vs. Frequency.

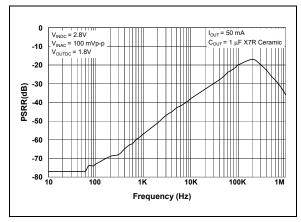


FIGURE 2-19: Power Supply Rejection Ratio vs. Frequency.

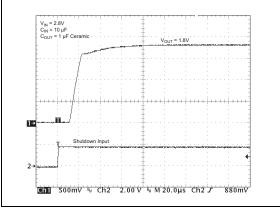


FIGURE 2-20:



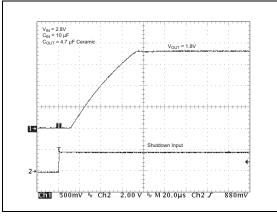


FIGURE 2-21:

Wake-Up Response.

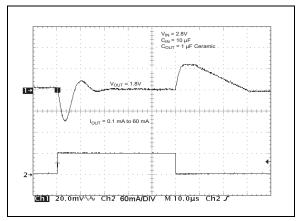


FIGURE 2-22: Load Transient Response.

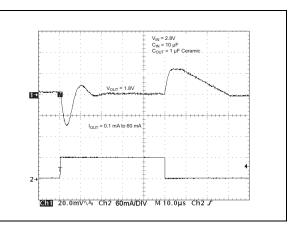


FIGURE 2-23: Load Transient Response.

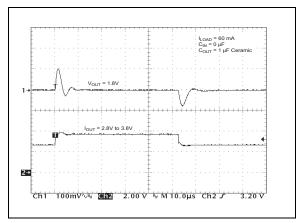


FIGURE 2-24: Line Transient Response.

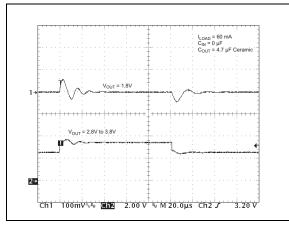


FIGURE 2-25:

Line Transient Response.

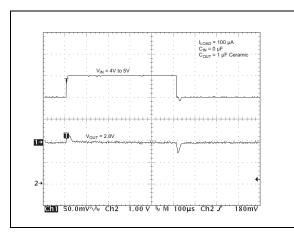


FIGURE 2-26: Line Transient Response.

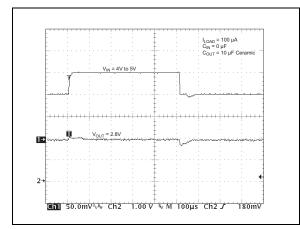


FIGURE 2-27:

Line Transient Response.

# 3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

5-Pin SC-70	Pin No. 5-Pin SOT-23	Name	Function
1	3	SHDN	Shutdown control input
2	4	NC	No connect
3	2	GND	Ground terminal
4	5	V <sub>OUT</sub>	Regulated voltage output
5	1	V <sub>IN</sub>	Unregulated supply input

#### TABLE 3-1: PIN FUNCTION TABLE

### 3.1 Shutdown Control Input (SHDN)

The regulator is fully enabled when a logic-high is applied to  $\overline{SHDN}$ . The regulator enters shutdown when a logic-low is applied to this input. During shutdown, the output voltage falls to zero and the supply current is reduced to 0.05  $\mu$ A (typ.)

#### 3.2 Ground Terminal (GND)

For best performance, it is recommended that the ground pin be tied to a ground plane.

#### 3.3 Regulated Voltage Output (V<sub>OUT</sub>)

Bypass the regulated voltage output to GND with a minimum capacitance of 1  $\mu\text{F}.$  A ceramic bypass capacitor is recommended for best performance.

### 3.4 Unregulated Supply Input (VIN)

The minimum  $V_{IN}$  has to meet two conditions in order to ensure that the output maintains regulation:  $V_{IN} \geq 2.7V$  and  $V_{IN} \geq [(V_R + 2.5\%) + V_{DROPOUT}]$ . The maximum  $V_{IN}$  should be less than or equal to 6V. Power dissipation may limit  $V_{IN}$  to a lower potential in order to maintain a junction temperature below 125°C. Refer to Section 5.0 "Thermal Considerations", for determining junction temperature.

It is recommended that  $\mathsf{V}_{\mathsf{IN}}$  be bypassed to GND with a ceramic capacitor.

### 4.0 DETAILED DESCRIPTION

The TC1016 is a precision, fixed-output, linear voltage regulator. The internal linear pass element is a P-channel MOSFET. As with all P-channel CMOS LDOs, there is a body drain diode, with the cathode connected to  $V_{IN}$  and the anode connected to  $V_{OUT}$  (Figure 4-1).

As shown in Figure 4-1, the output voltage of the LDO is sensed and divided down internally to reduce external component count. The internal error amplifier has a fixed, band gap reference on the inverting input, with the sensed output voltage on the noninverting input. The error amplifier output will pull the gate voltage down until the inputs of the error amplifier are equal in order to regulate the output voltage.

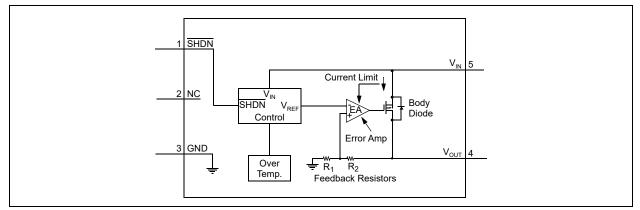
By sensing the current in the P-channel MOSFET, the maximum current delivered to the load is limited to a typical value of 120 mA, preventing excessive current from damaging the Printed Circuit Board (PCB) in the event of a shorted or faulted load.

An internal thermal sensing device is used to monitor the junction temperature of the LDO. When the sensed temperature is over the set threshold of 160°C (typ.), the P-channel MOSFET is turned off. When the MOSFET is off, the power dissipation internal to the device is almost zero. The device cools until the junction temperature is approximately 150°C and the MOSFET is turned on. If the internal power dissipation is still high enough for the junction to rise to 160°C, it will again shut off and cool. The maximum operating junction temperature of the device is 125°C. Steadystate operation at or near the 160°C overtemperature point can lead to permanent damage of the device.

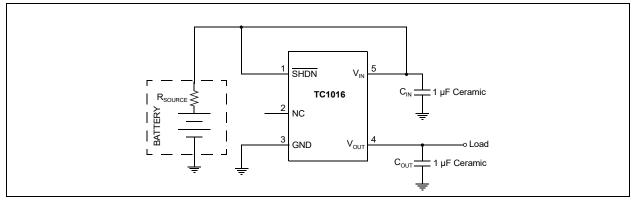
The output voltage  $(V_{OUT})$  remains stable over the entire input operating voltage range (2.7V to 6.0V), as well as the entire load range (0 mA to 80 mA). The output voltage is sensed through an internal resistor divider and compared with a precision internal voltage reference. Several fixed-output voltages are available by changing the value of the internal resistor divider.

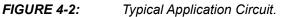
Figure 4-2 shows a typical application circuit. The regulator is enabled anytime the shutdown input pin is at or above  $V_{IH}$ , and shutdown (disabled) anytime the shutdown input pin is below  $V_{IL}$ . For applications where the SHDN feature is not used, tie the SHDN pin directly to the input supply voltage source. While in shutdown, the supply current decreases to 0.05 µA (typ.) and the P-channel MOSFET is turned off.

As shown in Figure 4-2, batteries have internal source impedance. An input capacitor in used to lower the input impedance of the LDO. In some applications, high input impedance can cause the LDO to become unstable. Adding more input capacitance can compensate for this.









#### 4.1 Input Capacitor

Low input source impedance is necessary for the LDO to operate properly. When operating from batteries, or in applications with long lead length (> 10") between the input source and the LDO, some input capacitance is required. A minimum of 0.1  $\mu$ F is recommended for most applications and the capacitor should be placed as close to the input of the LDO as is practical. Larger input capacitors will help reduce the input impedance and further reduce any high-frequency noise on the input and output of the LDO.

#### 4.2 Output Capacitor

A minimum output capacitance of 1  $\mu$ F for the TC1016 is required for stability. The ESR requirements on the output capacitor are between 0 and 2 ohms. The output capacitor should be located as close to the LDO output as is practical. Ceramic materials X7R and X5R have low temperature coefficients and are well within the acceptable ESR range required. A typical 1  $\mu$ F X5R 0805 capacitor has an ESR of 50 milli-ohms. Larger output capacitors can be used with the TC1016 to improve dynamic behavior and input ripple rejection performance.

Ceramic, aluminum electrolytic or tantalum capacitor types can be used. Since many aluminum electrolytic capacitors freeze at approximately -30°C, ceramic or solid tantalums are recommended for applications operating below -25°C. When operating from sources other than batteries, supply noise rejection and transient response can be improved by increasing the value of the input and output capacitors, and by employing passive filtering techniques.

#### 4.3 Turn-On Response

The turn on response is defined as two separate response categories, Wake-up Time  $(t_{\rm WK})$  and Settling Time  $(t_{\rm S}).$ 

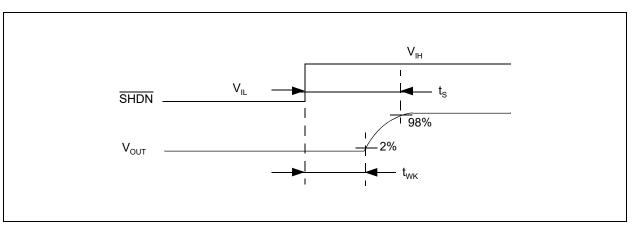
The TC1016 has a fast  $t_{WK}$  (10 µsec, typ.) when released from shutdown. Figure 4-3 provides the TC1016's  $t_{WK}$ . The  $t_{WK}$  is defined as the time it takes for the output to rise to 2% of the V<sub>OUT</sub> value after being released from shutdown.

The total turn-on response is defined as the  $t_{\rm S}$  (see Figure 4-3). The  $t_{\rm S}$  (inclusive with  $t_{\rm WK}$ ) is defined as the condition when the output is within 98% of its fully enabled value (42  $\mu sec,$  typ.) when released from shutdown. The settling time of the output voltage is dependent on load conditions and output capacitance on  $V_{OUT}$  (RC response).

Table 4-1 demonstrates the typical turn-on response timing for different input voltage power-up frequencies:  $V_{OUT}$  = 2.8V,  $V_{IN}$  = 5.0V,  $I_{OUT}$  = 60 mA and  $C_{OUT}$  = 1 µF.

TABLE 4-1:	<b>TYPICAL TURN-ON</b>
	<b>RESPONSE TIMING</b>

Frequency	Typical (t <sub>WK</sub> )	Typical (t <sub>S</sub> )
1000 Hz	5.3 µsec	14 µsec
500 Hz	5.9 µsec	16 µsec
100 Hz	9.8 µsec	32 µsec
50 Hz	14.5 µsec	52 µsec
10 Hz	17.2 µsec	77 µsec





Wake-Up Time from Shutdown.

### 5.0 THERMAL CONSIDERATIONS

#### 5.1 Thermal Shutdown

Integrated thermal-protection circuitry shuts the regulator off when die temperature exceeds approximately 160°C. The regulator remains off until the die temperature drops to approximately 150°C.

#### 5.2 Power Dissipation

The TC1016 is available in the SC-70 package. The thermal resistance for the SC-70 package is approximately 450°C/W when the copper area used in the PCB layout is similar to the JEDEC J51-7 high thermal conductivity or Semi G42-88 standards. For applications with larger or thicker copper areas, the thermal resistance can be lowered. See AN792 "A Method to Determine How Much Power a SOT23 Can Dissipate in an Application" (DS0000792), for a method to determine the thermal resistance for a particular application.

The TC1016 power dissipation capability is dependant upon several variables: input voltage, output voltage, load current, ambient temperature and maximum junction temperature. The absolute maximum steadystate junction temperature is rated at 125°C. The power dissipation within the device is equal to:

#### EQUATION 5-1:

$$P_D = (V_{IN} - V_{OUT}) \times I_{LOAD} + V_{IN} \times I_{GND}$$

The V<sub>IN</sub> x I<sub>GND</sub> term is typically very small when compared to the (V<sub>IN</sub>-V<sub>OUT</sub>) x I<sub>LOAD</sub> term simplifying the power dissipation within the LDO to be:

#### EQUATION 5-2:

$$P_D = (V_{IN} - V_{OUT}) \times I_{LOAD}$$

To determine the maximum power dissipation capability, the following equation is used:

**EQUATION 5-3:** 

$$P_{DMAX} = \frac{(T_{J MAX} - T_{A MAX})}{R\theta_{JA}}$$

Where:

 $T_{J\_MAX}$  = maximum junction temperature allowed  $T_{A\_MAX}$  = the maximum ambient temperature allowed  $R\theta_{JA}$  = the thermal resistance from junction-to-air Given the following example:

$$V_{IN} = 3.0V \text{ to } 4.1V$$

$$V_{OUT} = 2.8V \pm 2.5\%$$

$$I_{LOAD} = 60 \text{ mA (output current)}$$

$$T_{AMAX} = 55^{\circ}\text{C (max. ambient temp.)}$$

Find:

1. Internal power dissipation:

$$P_{DMAX} = (V_{\text{IN}\_\text{MAX}} - V_{\text{OUT}\_\text{MIN}}) \times I_{LOAD}$$
$$= (4.1V - 2.8 \times (0.975)) \times 60mA$$
$$= 82.2mW$$

2. Junction temperature:

$$T_{J_{MAX}} = P_{DMAX} \times R\theta_{JA}$$
  
= 82.2mWatts × 450°C/W +  $T_{AMAX}$   
= 37°C + 55°C  
= 92°C

3. Maximum allowable dissipation:

$$P_D = \frac{T_{J_MAX} - T_{A_MAX}}{R\theta_{JA}}$$
$$= \frac{125^{\circ}C - 55^{\circ}C}{450^{\circ}C/W}$$
$$= 155 mW$$

In this example, the TC1016 dissipates approximately 82.2 mW and the junction temperature is raised  $37^{\circ}$ C over the 55°C ambient to 92°C. The absolute maximum power dissipation is 155 mW when given a maximum ambient temperature of 55°C.

Input voltage, output voltage or load current limits can also be determined by substituting known values in Equation 5-2 and Equation 5-3.

#### 5.3 Layout Considerations

The primary path for heat conduction out of the SC-70 package is through the package leads. Using heavy, wide traces at the pads of the device will facilitate the removal of heat within the package, thus lowering the thermal resistance  $R\theta_{JA}$ . By lowering the thermal resistance, the maximum internal power dissipation capability of the package is increased.

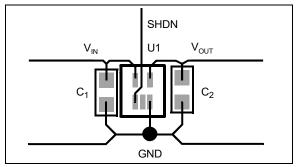
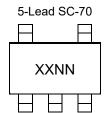


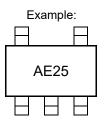
FIGURE 5-1: Suggested Layout

# 6.0 PACKAGE INFORMATION

#### 6.1 Package Marking Information



Part Number	Code		
TC1016-1.8VLTTR	AE		
TC1016-1.85VLTTR	AW		
TC1016-2.6VLTTR	AF		
TC1016-2.7VLTTR	AG		
TC1016-2.8VLTTR	AH		
TC1016-2.85VLTTR	AJ		
TC1016-2.9VLTTR	AK		
TC1016-3.0VLTTR(-VAO)	AL		
TC1016-3.3VLTTR	AM		
TC1016-4.0VLTTR	AP		
Note 1: The content of this table			



**Note 1:** The content of this table applies to the SC-70 package.

#### 5-Lead SOT-23

XXNN

Part Number	Code		
TC1016-1.8VCTTR	НК		
TC1016-1.85VCTTR	HW		
TC1016-2.6VCTTR	HL		
TC1016-2.7VCTTR	HM		
TC1016-2.8VCTTR	HP		
TC1016-2.85VCTTR	HQ		
TC1016-2.9VCTTR	HR		
TC1016-3.0VCTTR	HS		
TC1016-3.3VCTTR	HT		
TC1016-4.0VCTTR	HU		
<b>Note 1</b> : The content of this table			

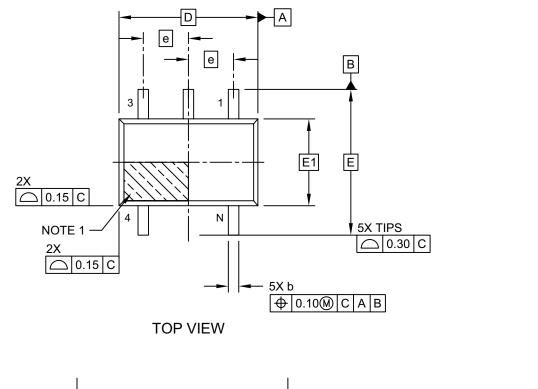
**Note 1:** The content of this table applies to the SOT-23 package.

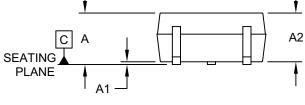
Exa	mple
Н	(25

Legend:	XXX	Product Code or Customer-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week '01')
	NNN	Alphanumeric traceability code
	Pb-free JEDEC designator for Matte Tin (Sn)	
	(e3) *	This package is Pb-free. The Pb-free JEDEC designator (i)
		can be found on the outer packaging for this package.
	be carried	nt the full Microchip part number cannot be marked on one line, it will over to the next line, thus limiting the number of available s for customer-specific information. Package may or not include the logo.

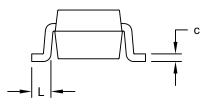
# 5-Lead Plastic Small Outline Transistor (LT) [SC70]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging





SIDE VIEW



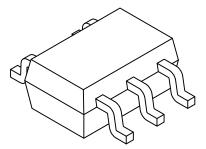
END VIEW

Microchip Technology Drawing C04-061-LT Rev E Sheet 1 of 2

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#### 5-Lead Plastic Small Outline Transistor (LT) [SC70]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS					
Dimension	Dimension Limits			MAX		
Number of Pins	N		5			
Pitch	е		0.65 BSC			
Overall Height	Α	0.80 - 1.10				
Standoff	A1	0.00	-	0.10		
Molded Package Thickness	A2	0.80 - 1.00				
Overall Length	D	2.00 BSC				
Overall Width	E	2.10 BSC				
Molded Package Width	E1	1.25 BSC				
Terminal Width	b	0.15	-	0.40		
Terminal Length	L	0.10	0.20	0.46		
Lead Thickness	С	0.08 - 0.26				

Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- 3. Dimensioning and tolerancing per ASME Y14.5M
  - BSC: Basic Dimension. Theoretically exact value shown without tolerances.

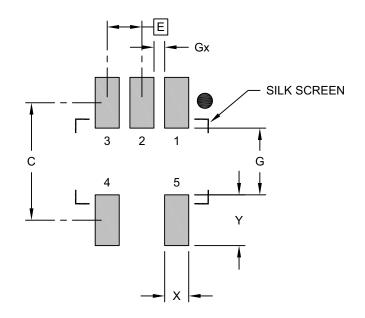
REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-061-LT Rev E Sheet 2 of 2

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# 5-Lead Plastic Small Outline Transistor (LT) [SC70]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



#### **RECOMMENDED LAND PATTERN**

	Units		MILLIMETERS			
Dimension	n Limits	MIN	NOM	MAX		
Contact Pitch	E		0.65 BSC			
Contact Pad Spacing	С		2.20			
Contact Pad Width	Х			0.45		
Contact Pad Length	Y			0.95		
Distance Between Pads	G	1.25				
Distance Between Pads	Gx	0.20				

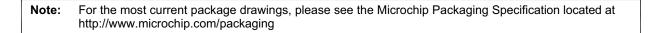
Notes:

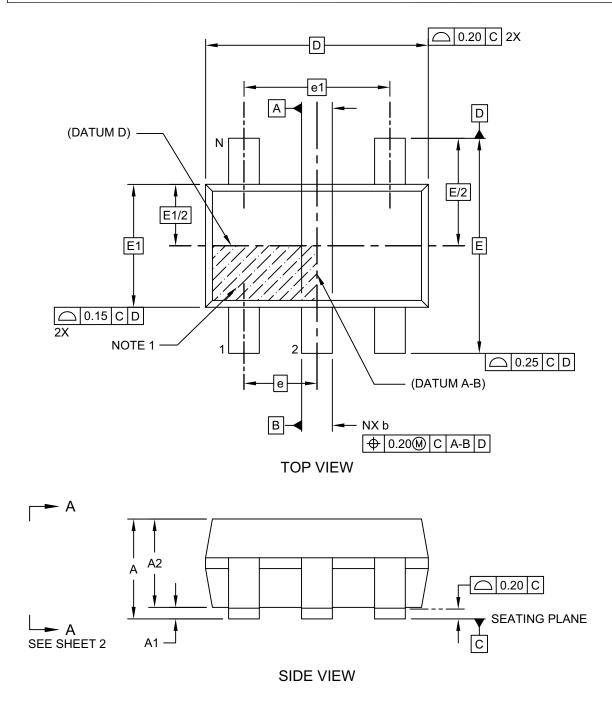
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

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### 5-Lead Plastic Small Outline Transistor (C7X) [SOT-23]

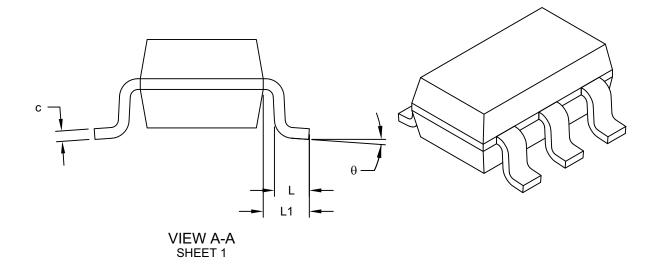




Microchip Technology Drawing C04-091-C7X Rev H Sheet 1 of 2

# 5-Lead Plastic Small Outline Transistor (C7X) [SOT-23]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	Ν	<b>IILLIMETER</b>	S
Dimension	Limits	MIN	NOM	MAX
Number of Pins	N	5		
Pitch	е	0.95 BSC		
Outside lead pitch	e1	1.90 BSC		
Overall Height	Α	0.90	-	1.45
Molded Package Thickness	A2	0.89	-	1.30
Standoff	A1	-	-	0.15
Overall Width	E	2.80 BSC		
Molded Package Width	E1	1.60 BSC		
Overall Length	D	2.90 BSC		
Foot Length	L	0.30	-	0.60
Footprint	L1	0.60 REF		
Foot Angle	θ	0°	-	10°
Lead Thickness	С	0.08	-	0.26
Lead Width	b	0.20	-	0.51

Notes:

1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.25mm per side.

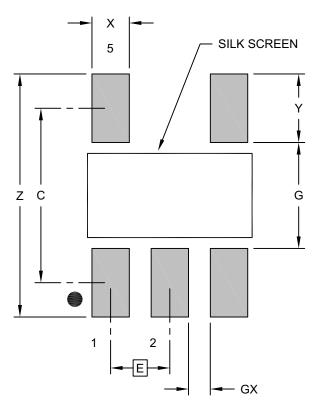
BSC: Basic Dimension. Theoretically exact value shown without tolerances. REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-091-C7X Rev H Sheet 2 of 2

<sup>2.</sup> Dimensioning and tolerancing per ASME Y14.5M

# 5-Lead Plastic Small Outline Transistor (C7X) [SOT-23]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



#### RECOMMENDED LAND PATTERN

	Units	MILLIMETERS		
Dimension	Limits	MIN	NOM	MAX
Contact Pitch	Е		0.95 BSC	
Contact Pad Spacing	С		2.80	
Contact Pad Width (X5)	Х			0.60
Contact Pad Length (X5)	Y			1.10
Distance Between Pads	G	1.70		
Distance Between Pads	GX	0.35		
Overall Width	Ζ			3.90

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2091-C7X Rev H

NOTES:

# APPENDIX A: REVISION HISTORY

#### **Revision D (October 2023)**

- Added automotive qualification to Features and examples to Product Identification System.
- Added ESD values to Section 1.0 "Electrical Characteristics".
- Updated Section 6.0 "Package Information".
- Minor style updates.

#### **Revision C (December 2012)**

• Added a note to each package outline drawing.

#### **Revision B (March 2005)**

- Updated Section 6.0 "Package Information" to include old and new packaging examples, as well as replaced SC-70 package diagram with up-todate version. Added additional voltage options
- Added SOT-23 package and voltage options.
- Applied new template and rearranged sections to be consistent with current documentation.

#### .Revision A (October 2001)

• Original Release of this Document.

NOTES:

### **PRODUCT IDENTIFICATION SYSTEM**

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

Option	5V / /	utdown	b) TC1(	016-1.8VCTTR: 016-1.8VLTTR: 016-1.85VCTTR:	80 mA Tiny CMOS LDO with Shutdown, SOT-23 package 80 mA Tiny CMOS LDO with Shutdown, SC-70 package		
Voltage Options*: 1.8V (Standard) 1.85 2.6V 2.7V 2.8V 2.8S	/ 5V /		,		80 mA Tiny CMOS LDO with Shutdown, SC-70 package		
(Standard) 1.85 2.6V 2.7V 2.8V 2.85	5V / /		c) TC1(	016-1.85VCTTR:			
2.7V 2.8V 2.85	/				80 mA Tiny CMOS LDO with Shutdown, SOT-23 package		
	/	C	d) TC1(	016-2.6VLTTR:	80 mA Tiny CMOS LDO with Shutdown, SC-70 package		
3.0\	/	e	e) TC1(	016-2.7VCTTR:	80 mA Tiny CMOS LDO with Shutdown, SOT-23 package		
3.3V 4.0V	/		f) TC1(	016-2.7VLTTR:	80 mA Tiny CMOS LDO with Shutdown, SC-70 package		
loca	e Package Marking Information. Please al Microchip sales office to request othe tions.		g) TC1(	016-2.8VCTTR:	80 mA Tiny CMOS LDO with Shutdown, SOT-23 package		
Temperature Range: V	= -40°C to +125°C	ľ	h) TC1(	016-2.8VLTTR:	80 mA Tiny CMOS LDO with Shutdown, SC-70 package		
Packages: LT CT	= 5-Lead SC-70 = 5-Lead SOT-23	i	i) TC1(	016-2.85VLTTR:	80 mA Tiny CMOS LDO with Shutdown, SC-70 package		
Tape and Reel TR Option <sup>(1)</sup> :	= Tape an Reel, 3000/Reel (SC-70	) or SOT-23) j	j) TC10	016-3.0VLTTR-VAO:	80 mA Tiny CMOS LDO with Shutdown, SC-70 package, AEC-Q100 Automotive Qualified		
Qualification**: (Bla VAC	nk) = Standard Part ) = AEC-Q100 Automotive Qualified	1					
**Cu	urrently available VAO variants are show ples.	wn in Exam-	Note	catalog part nu identifier is use	identifier only appears in the mber description. This d for ordering purposes and		
Contact your local Microchip sales office to automotive qualified variants for other pack voltage options.				with your Micro	is not printed on the device package. Check with your Microchip Sales Office for package availability with the Tape and Reel option.		

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